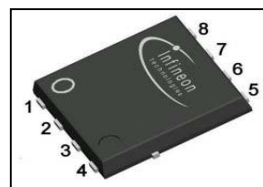


**OptiMOS™3 Power-MOSFET**
**Features**

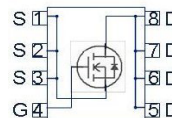
- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Improved switching behaviour
- Qualified according to JEDEC<sup>1)</sup> for target applications
- N-channel; Logic level
- Excellent gate charge  $\times R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- Superior thermal resistance
- Avalanche rated
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

**Product Summary**

|                  |     |            |
|------------------|-----|------------|
| $V_{DS}$         | 30  | V          |
| $R_{DS(on),max}$ | 4.3 | m $\Omega$ |
| $I_D$            | 87  | A          |

**PG-TDSON-8**


| Type           | Package    | Marking  |
|----------------|------------|----------|
| BSC043N03LSC G | PG-TDSON-8 | 043N03LS |



**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                                     | Symbol        | Conditions                                                          | Value    | Unit |
|-----------------------------------------------|---------------|---------------------------------------------------------------------|----------|------|
| Continuous drain current                      | $I_D$         | $V_{GS}=10\text{ V}, T_C=25\text{ °C}$                              | 87       | A    |
|                                               |               | $V_{GS}=10\text{ V}, T_C=100\text{ °C}$                             | 55       |      |
|                                               |               | $V_{GS}=4.5\text{ V}, T_C=25\text{ °C}$                             | 69       |      |
|                                               |               | $V_{GS}=4.5\text{ V}, T_C=100\text{ °C}$                            | 44       |      |
|                                               |               | $V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=50\text{ K/W}^{2)}$ | 16       |      |
| Pulsed drain current <sup>3)</sup>            | $I_{D,pulse}$ | $T_C=25\text{ °C}$                                                  | 348      |      |
| Avalanche current, single pulse <sup>4)</sup> | $I_{AS}$      | $T_C=25\text{ °C}$                                                  | 50       |      |
| Avalanche energy, single pulse                | $E_{AS}$      | $I_D=35\text{ A}, R_{GS}=25\text{ }\Omega$                          | 40       | mJ   |
| Gate source voltage                           | $V_{GS}$      |                                                                     | $\pm 20$ | V    |

<sup>1)</sup> J-STD20 and JESD22

Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol                | Conditions                                                 | Value       | Unit |
|-------------------------------------|-----------------------|------------------------------------------------------------|-------------|------|
| Power dissipation                   | $P_{\text{tot}}$      | $T_C=25\text{ °C}$                                         | 28          | W    |
|                                     |                       | $T_A=25\text{ °C}$ ,<br>$R_{\text{thJA}}=50\text{ K/W}^2)$ | 2.5         |      |
| Operating and storage temperature   | $T_j, T_{\text{stg}}$ |                                                            | -55 ... 150 | °C   |
| IEC climatic category; DIN IEC 68-1 |                       |                                                            | 55/150/56   |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                     |                   |                                              |   |   |     |     |
|-------------------------------------|-------------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{\text{thJC}}$ | bottom                                       | - | - | 4.5 | K/W |
|                                     |                   | top                                          | - | - | 20  |     |
| Device on PCB                       | $R_{\text{thJA}}$ | 6 cm <sup>2</sup> cooling area <sup>2)</sup> | - | - | 50  |     |

Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |                             |                                                                                 |    |     |     |               |
|----------------------------------|-----------------------------|---------------------------------------------------------------------------------|----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$                            | 30 | -   | -   | V             |
| Gate threshold voltage           | $V_{\text{GS(th)}}$         | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{ }\mu\text{A}$              | 1  | -   | 2.2 |               |
| Zero gate voltage drain current  | $I_{\text{DSS}}$            | $V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$         | -  | 0.1 | 1   | $\mu\text{A}$ |
|                                  |                             | $V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$        | -  | 10  | 100 |               |
| Gate-source leakage current      | $I_{\text{GSS}}$            | $V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$                           | -  | 10  | 100 | nA            |
| Drain-source on-state resistance | $R_{\text{DS(on)}}$         | $V_{\text{GS}}=4.5\text{ V}, I_{\text{D}}=30\text{ A}$                          | -  | 5.4 | 6.7 | m $\Omega$    |
|                                  |                             | $V_{\text{GS}}=10\text{ V}, I_{\text{D}}=30\text{ A}$                           | -  | 3.6 | 4.3 |               |
| Gate resistance                  | $R_{\text{G}}$              |                                                                                 | -  | 1.4 | -   | $\Omega$      |
| Transconductance                 | $g_{\text{fs}}$             | $ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}, I_{\text{D}}=30\text{ A}$ | 39 | 78  | -   | S             |

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |                                                                                       |   |      |      |    |
|------------------------------|--------------|---------------------------------------------------------------------------------------|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$<br>$f=1\text{ MHz}$                          | - | 2300 | 3100 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                       | - | 790  | 1100 |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                       | - | 45   | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=30\text{ A}, R_G=1.6\text{ }\Omega$ | - | 5.5  | -    | ns |
| Rise time                    | $t_r$        |                                                                                       | - | 3.8  | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                       | - | 23   | -    |    |
| Fall time                    | $t_f$        |                                                                                       | - | 3.6  | -    |    |

**Gate Charge Characteristics<sup>5)</sup>**

|                              |               |                                                                             |   |      |    |    |
|------------------------------|---------------|-----------------------------------------------------------------------------|---|------|----|----|
| Gate to source charge        | $Q_{gs}$      | $V_{DD}=15\text{ V}, I_D=30\text{ A},$<br>$V_{GS}=0\text{ to }4.5\text{ V}$ | - | 6.8  | -  | nC |
| Gate charge at threshold     | $Q_{g(th)}$   |                                                                             | - | 3.5  | -  |    |
| Gate to drain charge         | $Q_{gd}$      |                                                                             | - | 3.2  | -  |    |
| Switching charge             | $Q_{sw}$      |                                                                             | - | 6.5  | -  |    |
| Gate charge total            | $Q_g$         |                                                                             | - | 13.7 | 18 |    |
| Gate plateau voltage         | $V_{plateau}$ |                                                                             | - | 3.1  | -  | V  |
| Gate charge total            | $Q_g$         | $V_{DD}=15\text{ V}, I_D=30\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$  | - | 28   | 38 | nC |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | $V_{DS}=0.1\text{ V},$<br>$V_{GS}=0\text{ to }4.5\text{ V}$                 | - | 11.9 | -  |    |
| Output charge                | $Q_{oss}$     | $V_{DD}=15\text{ V}, V_{GS}=0\text{ V}$                                     | - | 20   | -  |    |

**Reverse Diode**

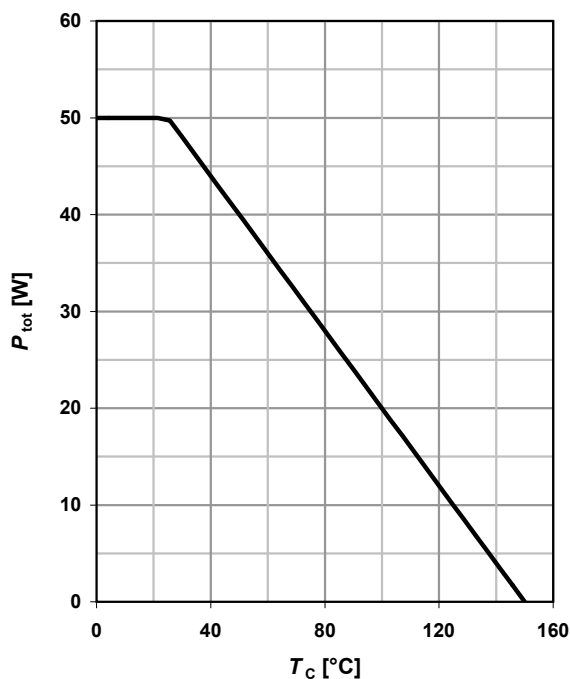
|                                  |               |                                                                         |   |      |     |    |
|----------------------------------|---------------|-------------------------------------------------------------------------|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$                                          | - | -    | 45  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                         | - | -    | 348 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=30\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 0.85 | -   | V  |
| Reverse recovery charge          | $Q_{rr}$      | $V_R=15\text{ V}, I_F=I_S,$<br>$di_F/dt=400\text{ A}/\mu\text{s}$       | - | -    | 10  | nC |

<sup>4)</sup> See figure 13 for more detailed information

<sup>5)</sup> See figure 16 for gate charge parameter definition

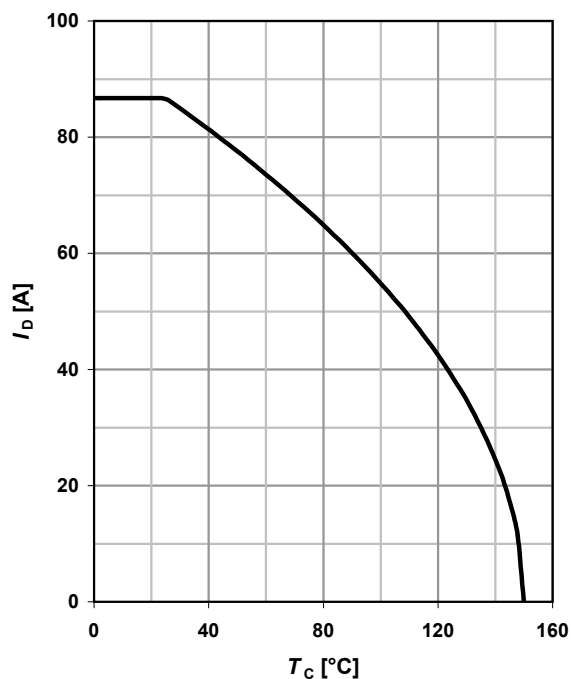
## 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



## 2 Drain current

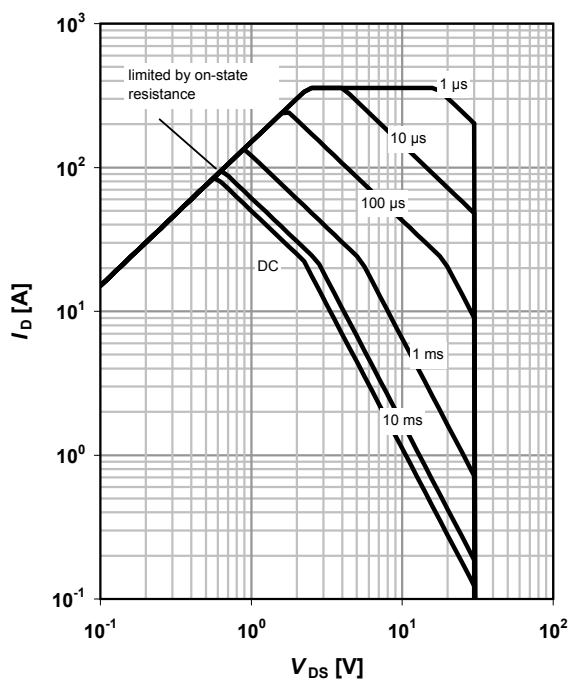
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



## 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

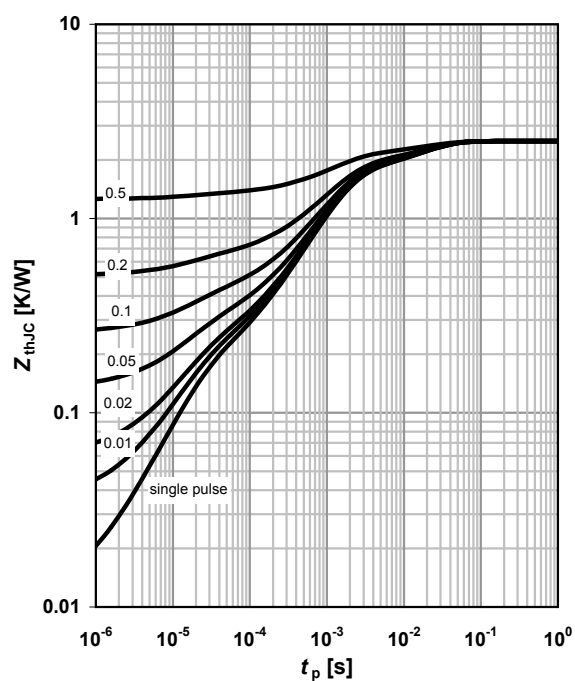
parameter:  $t_p$



## 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

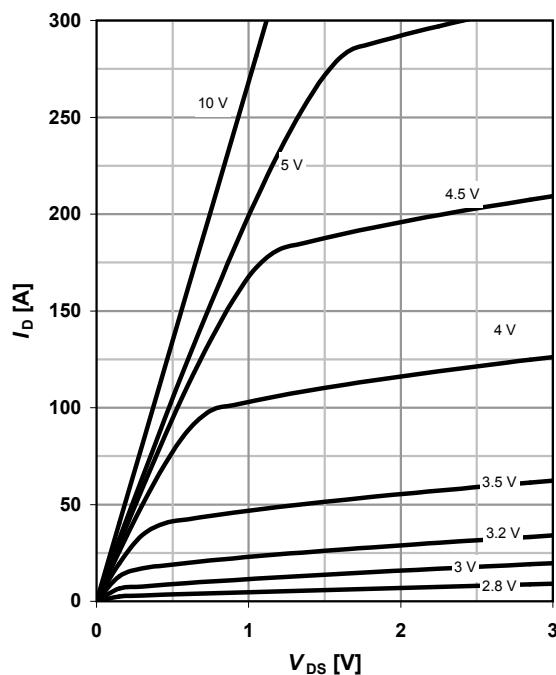
parameter:  $D = t_p / T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

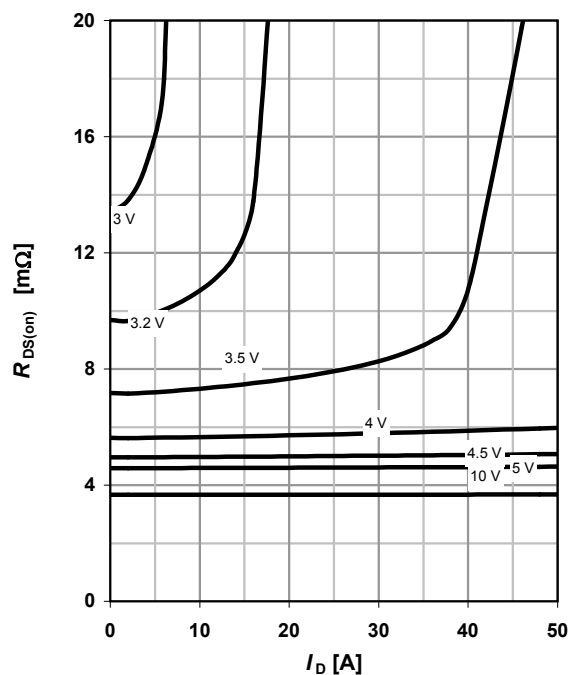
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

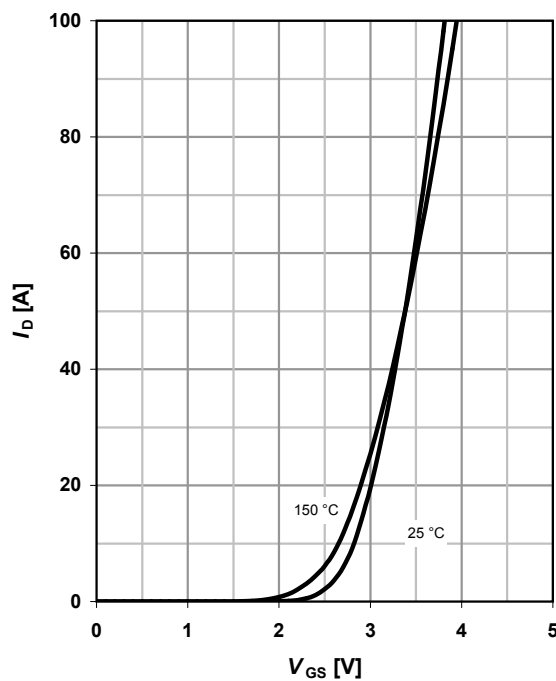
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

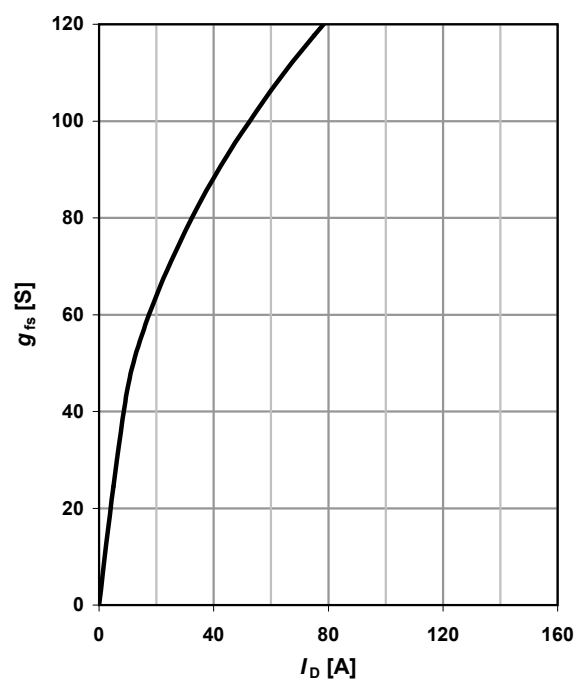
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_j$



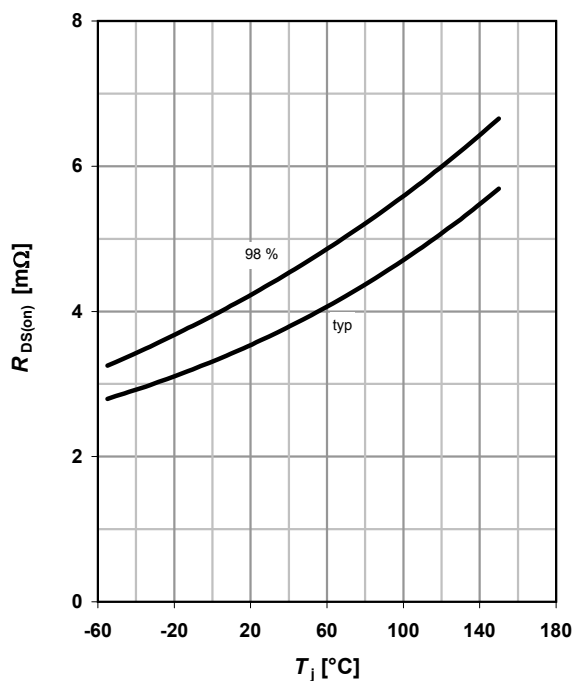
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$



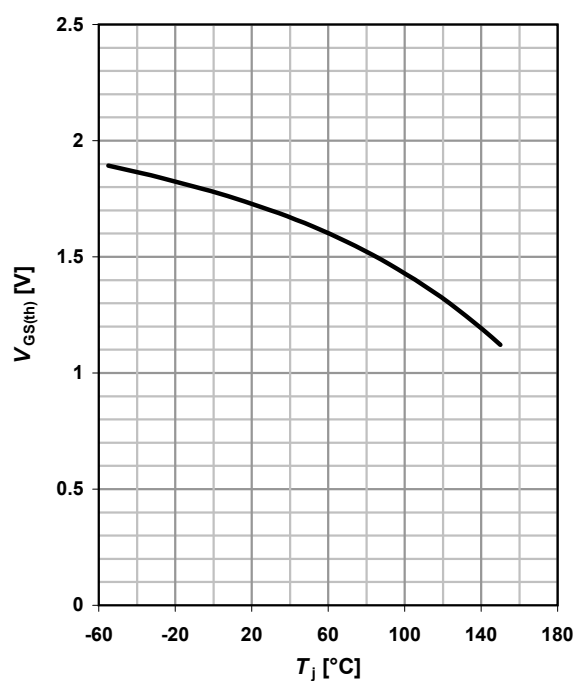
### 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j); I_D = 30 \text{ A}; V_{GS} = 10 \text{ V}$$



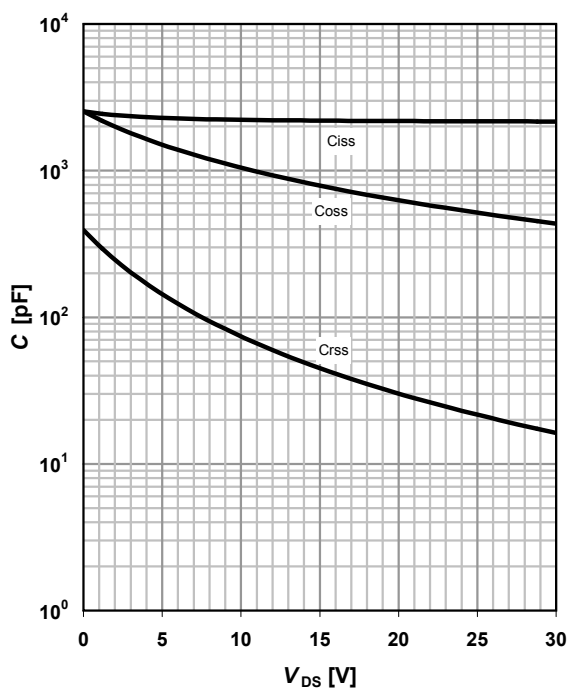
### 10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu\text{A}$$



### 11 Typ. capacitances

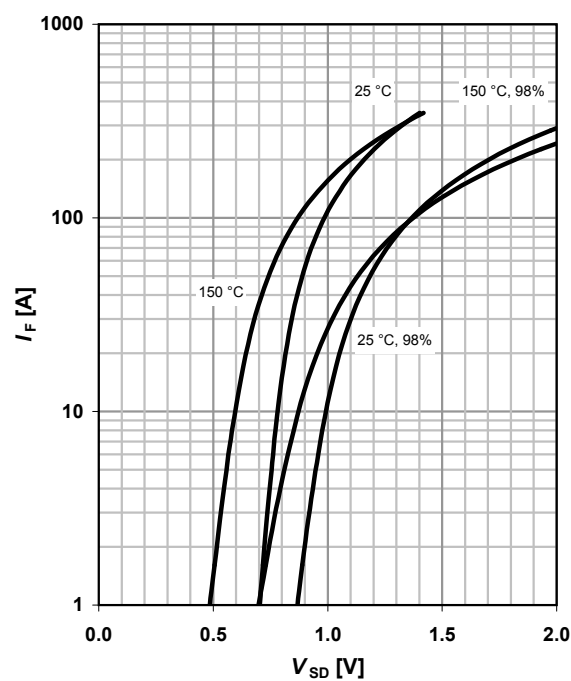
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



### 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

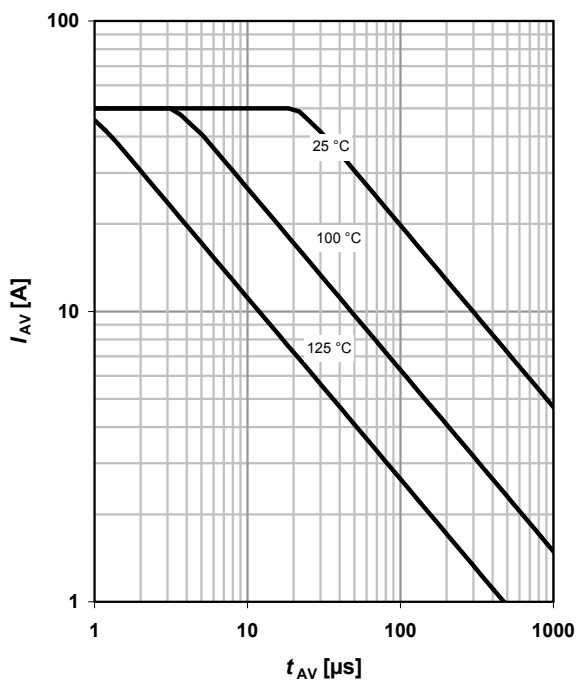
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

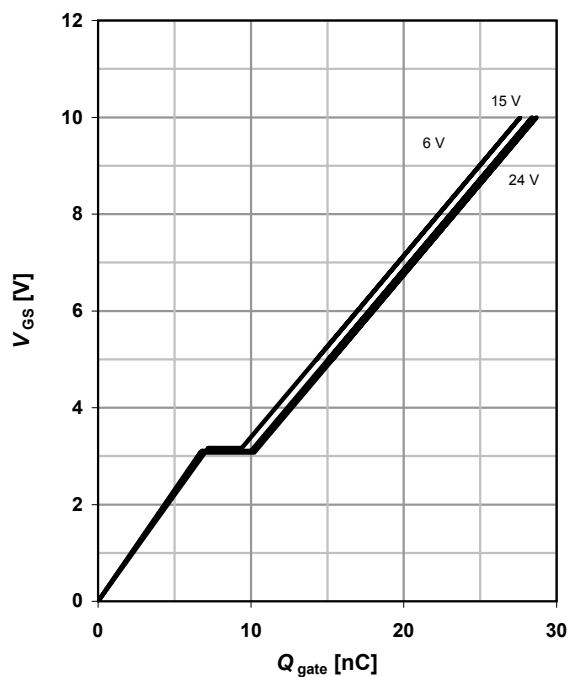
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

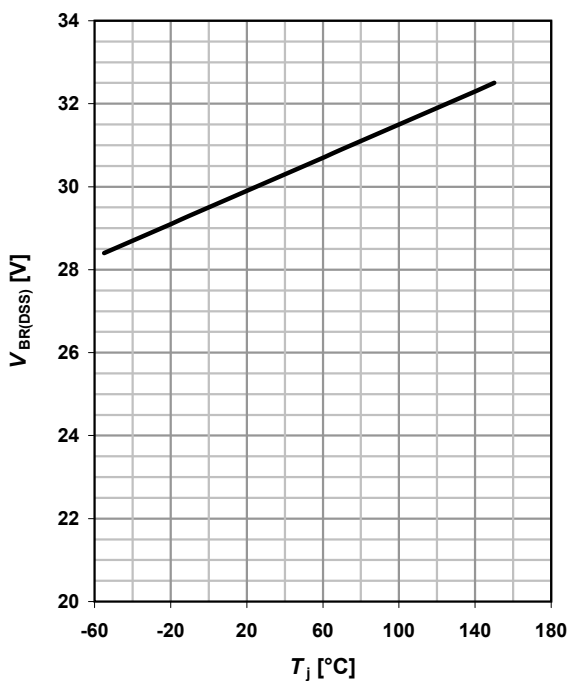
$$V_{GS}=f(Q_{\text{gate}}); I_D=30\ \text{A pulsed}$$

parameter:  $V_{DD}$



### 15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



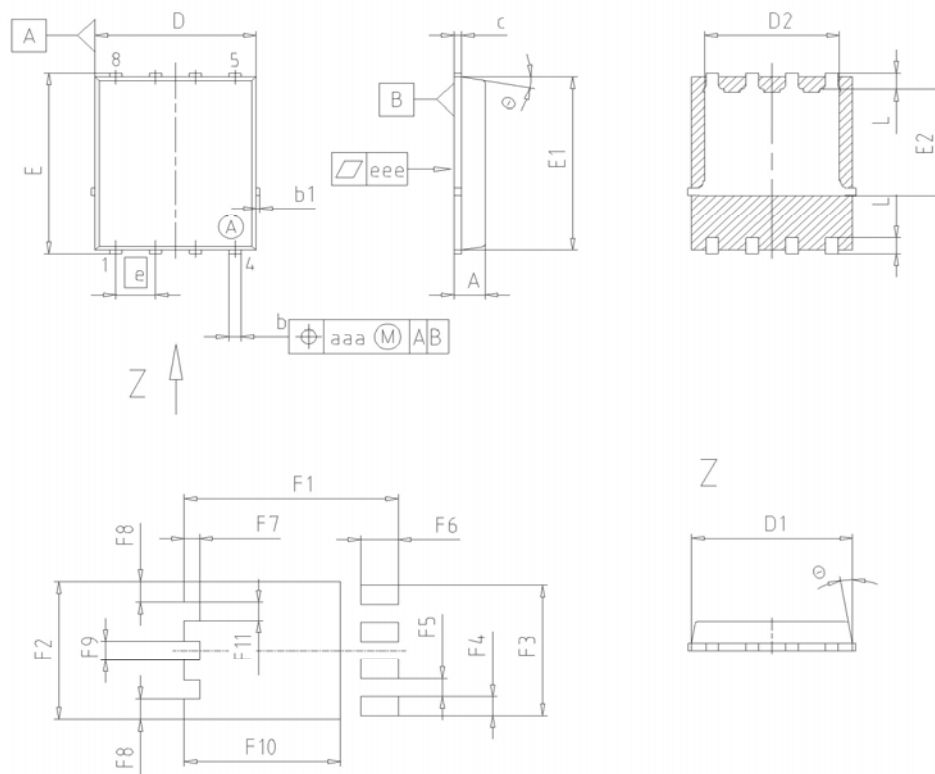
### 16 Gate charge waveforms



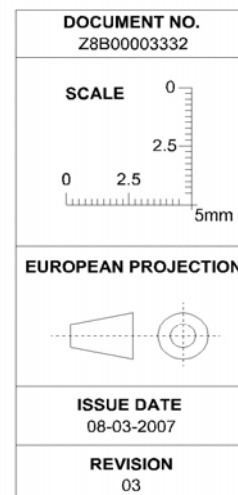
## Package Outline

## PG-TDSON-8

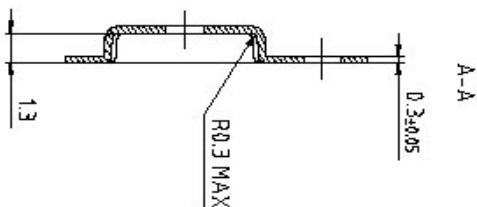
## PG-TDSON-8: Outline



| DIM  | MILLIMETERS |       | INCHES |       |
|------|-------------|-------|--------|-------|
|      | MIN         | MAX   | MIN    | MAX   |
| A    | 0.90        | 1.10  | 0.035  | 0.043 |
| b    | 0.34        | 0.54  | 0.013  | 0.021 |
| b1   | 0.02        | 0.22  | 0.001  | 0.008 |
| c    | 0.15        | 0.35  | 0.006  | 0.014 |
| D=D1 | 4.95        | 5.35  | 0.195  | 0.211 |
| D2   | 4.20        | 4.40  | 0.165  | 0.173 |
| E    | 5.95        | 6.35  | 0.234  | 0.250 |
| E1   | 5.70        | 6.10  | 0.224  | 0.240 |
| E2   | 3.40        | 3.80  | 0.134  | 0.150 |
| e    | 1.27        |       | 0.050  |       |
| N    | 8           |       | 8      |       |
| L    | 0.45        | 0.65  | 0.018  | 0.026 |
| □    | 8.5°        | 11.5° | 8.5°   | 11.5° |
| aaa  | 0.25        |       | 0.010  |       |
| eee  | 0.05        |       | 0.002  |       |
| F1   | 6.75        | 6.95  | 0.266  | 0.274 |
| F2   | 4.60        | 4.80  | 0.181  | 0.189 |
| F3   | 4.36        | 4.56  | 0.172  | 0.180 |
| F4   | 0.55        | 0.75  | 0.022  | 0.030 |
| F5   | 0.52        | 0.72  | 0.020  | 0.028 |
| F6   | 1.10        | 1.30  | 0.043  | 0.051 |
| F7   | 0.40        | 0.60  | 0.016  | 0.024 |
| F8   | 0.60        | 0.80  | 0.024  | 0.031 |
| F9   | 0.53        | 0.73  | 0.021  | 0.029 |
| F10  | 4.90        | 5.10  | 0.193  | 0.201 |
| F11  | 0.53        | 0.73  | 0.021  | 0.029 |



## PG-TDSON-8: Tape



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